Application Report

ISOS141-SEP Single-Event Latch-Up (SEL) Radiation Report

ABSTRACT

The purpose of this study is to characterize the effects of heavy-ion irradiation on the single-event latch-up (SEL) performance of the ISOS141-SEP, high-speed quad-channel digital isolator. Heavy-ions with an LET_{EFF} of 43 MeV-cm^2/mg were used to irradiate the devices with a fluence of 1×10^7 ions/cm^2. The results demonstrate that the ISOS141-SEP is SEL-free up to LET_{EFF} = 43 MeV-cm^2/mg at 125°C.

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1 Overview

The ISOS141-SEP is a high-speed, quad-channel digital isolator. The devices uses single-ended CMOS logic switching technology. The voltage range is from 2.25 V to 5.5 V for both supplies, V_{CC1} and V_{CC2}. ISOS141-SEP does not conform to any specific interface standard and is only intended for isolating single-ended CMOS or TTL digital signal lines. Each isolation channel has a logic input and output buffer separated by a double capacitive silicon dioxide (SiO_2) insulation barrier. This device comes with enable pins which sets the default output to low if the input power or signal is lost.

http://www.ti.com/product/ISOS141-SEP

Table 1-1. Overview Information(1)

DESCRIPTION	DEVICE INFORMATION
TI Part Number	ISOS141-SEP
MLS Number	ISOS141FDBQSEP
Device Function	Radiation Tolerant High-Speed Quad-Channel Digital Isolator
Technology	LBC8LVISO
Exposure Facility	Radiation Effects Facility, Cyclotron Institute, Texas A&M University
Heavy Ion Fluence per Run	1×10^6 – 1×10^7 ions/cm^2
Irradiation Temperature	125°C (for SEL testing)

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2 SEE Mechanisms

The primary single-event effect (SEE) events of interest in the ISOS141-SEP are the destructive single-event latch-up (SEL) and Single Event Dielectric Rupture (SEDR). From a risk/impact point-of-view, the occurrence of an SEL is potentially the most destructive SEE event and the biggest concern for space applications. The LBC8LVISO process node was used for the ISOS141-SEP. CMOS circuitry introduces a potential for SEL susceptibility. SEL can occur if excess current injection caused by the passage of an energetic ion is high enough to trigger the formation of a parasitic cross-coupled PNP and NPN bipolar structure (formed between the p-sub and n-well and n+ and p+ contacts). The parasitic bipolar structure initiated by a single-event creates a high-conductance path (inducing a steady-state current that is typically orders-of-magnitude higher than the normal operating current) between power and ground that persists (is "latched") until power is removed or until the device is destroyed by the high-current state. The process modifications applied for SEL-mitigation were sufficient as the ISOS141-SEP exhibited no SEL with heavy-ions up to an LET_{EFF} of 43 MeV-cm^2/mg at a fluence of 10^7 ions/cm^2 and a chip temperature of 125°C.

This study was performed to evaluate the SEL effects with a bias voltage of 5.5 V on V_S supply voltage. Heavy ions with LET_{EFF} = 43 MeV-cm^2/mg were used to irradiate the devices. Flux of 10^5 ions/s-cm^2 and fluence of 10^7 ions/cm^2 were used during the exposure at 125°C temperature.

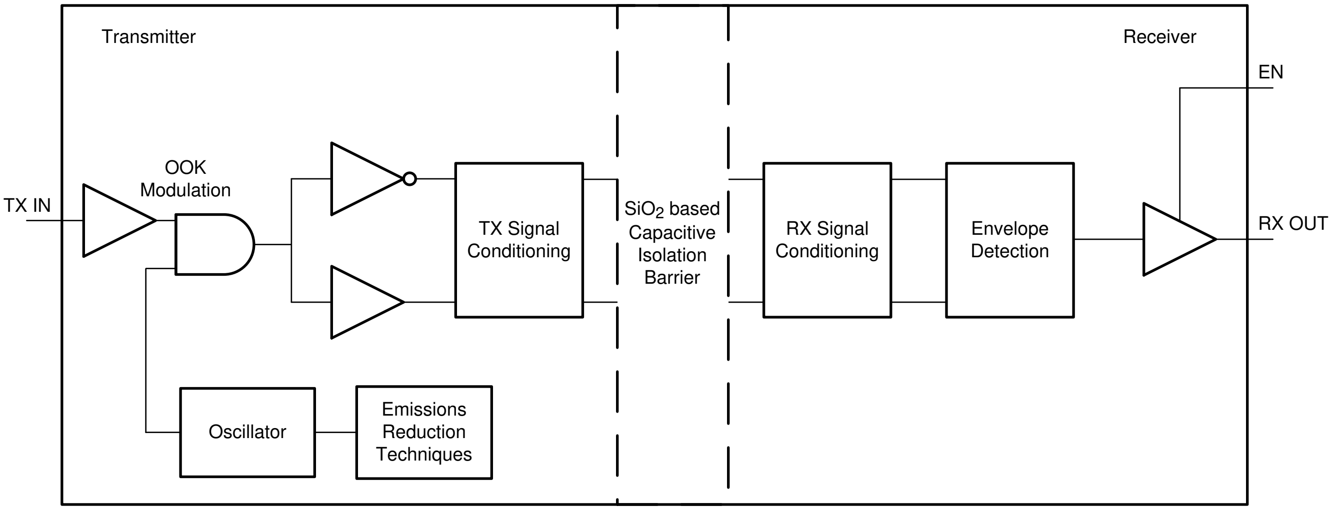

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Figure 2-1. Functional Block Diagram of the ISOS141-SEP

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3 Test Device and Test Board Information

The ISOS141-SEP is packaged in an 16-pin, QSOP shown with pinout in Figure 3-1. Figure 3-2 shows the ISOS141-SEP bias diagram.

ISOS141-SEP pinout diagram. The package was decap'ed to reveal the die face for all heavy ion testing.

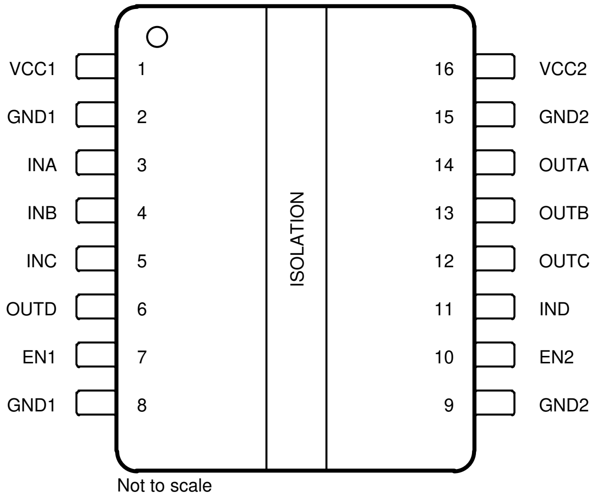

Figure 3-1. ISOS141-SEP Pinout Diagram

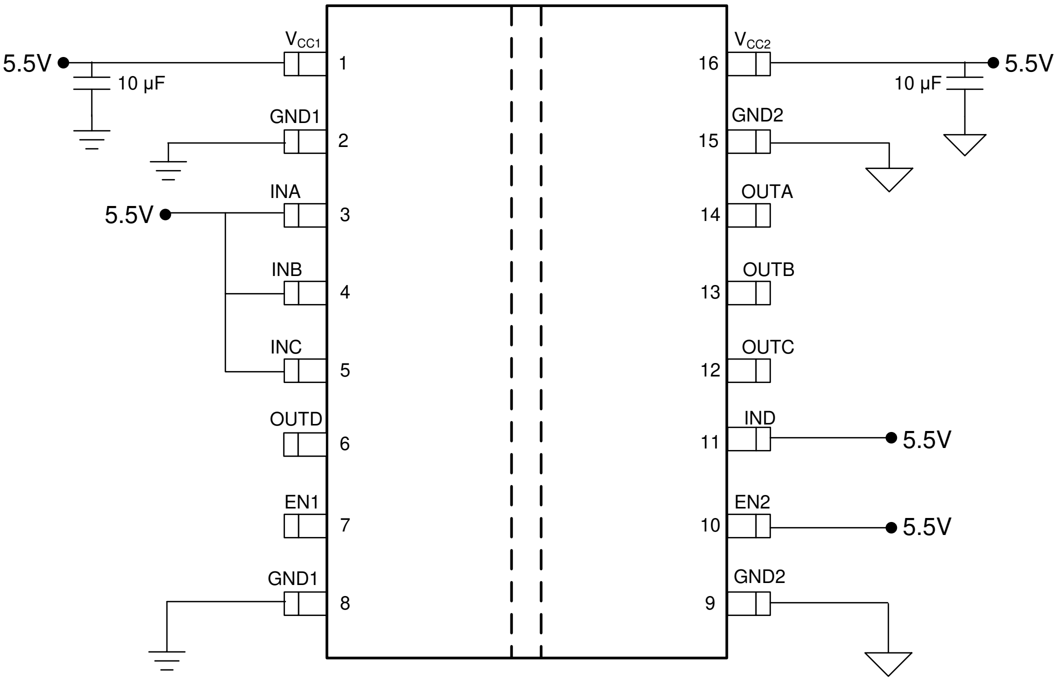

Figure 3-2. ISOS141-SEP SEL Bias Diagram

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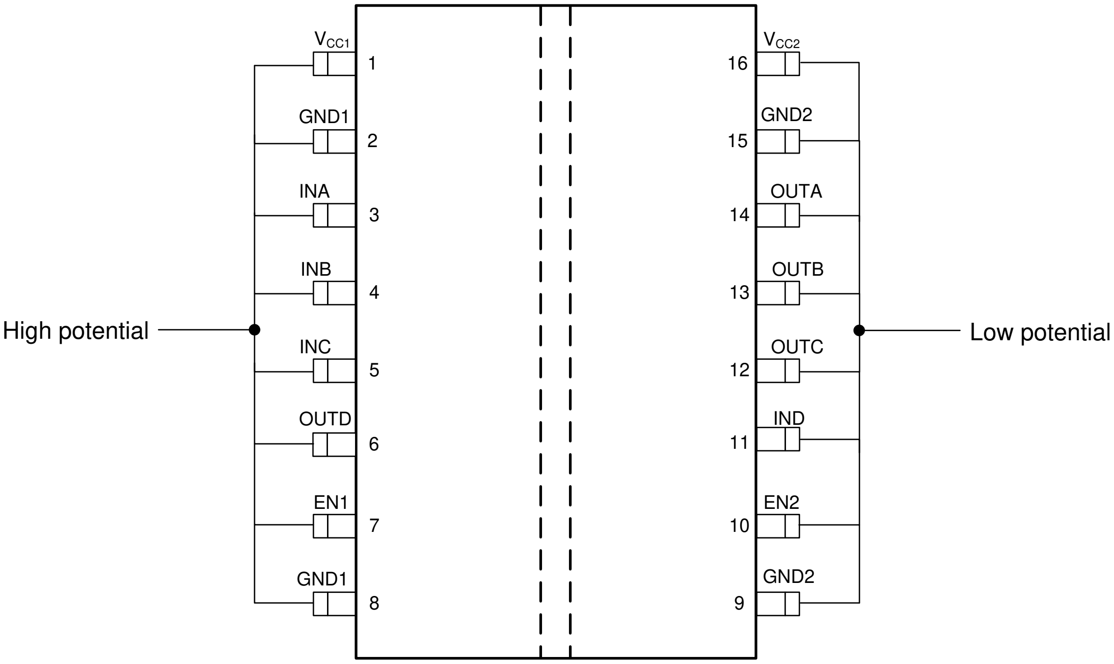

Figure 3-3. ISOS141-SEP SEDR Bias Diagram

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4 Irradiation Facility and Setup

The heavy ion species used for the SEE studies on this product were provided and delivered by the TAMU Cyclotron Radiation Effects Facility [3] using a superconducting cyclotron and advanced electron cyclotron resonance (ECR) ion source. Ion beams are delivered with high uniformity over a 1-inch diameter circular cross sectional area for the in-air station. Uniformity is achieved by means of magnetic defocusing. The intensity of the beam is regulated over a broad range spanning several orders of magnitude. For the bulk of these studies, ion fluxes between 10^4 and 10^5 ions/s-cm^2 were used to provide heavy ion fluences between 10^6 and 10^7 ions/cm^2. For these experiments Silver (Ag) ions were used. Ion beam uniformity for all tests was in the range of 91% to 98%.

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5 Results

5.1 SEL Results

During SEL characterization, the device was heated using forced hot air, maintaining the IC temperature at 125°C. The temperature was monitored by means of a K-type thermocouple attached as close to the IC as possible. The species used for the SEL testing was a silver (^{47}Ag) ion with an angle-of-incidence of 0° for an LET_{EFF} = 43 MeV-cm^2/mg. The kinetic energy in the vacuum for this ion is 1.634 GeV (15-MeV/amu line). A flux of approximately 10^5 ions/cm^2-s and a fluence of approximately 10^7 ions were used for two runs. The Vs supply voltage is supplied externally onboard at the recommended maximum voltage setting of 5.5 V. Run duration to achieve this fluence was approximately 2 minutes. No SEL events were observed during all four runs shown in Table 5-1. Figure 5-1 shows a plot of the current vs time.

Table 5-1. ISOS141-SEP SEL Conditions Using^{47}Ag at an Angle-of-Incidence of 0°

RUN #	DISTANCE (mm)	TEMPERATURE (°C)	ION	ANGLE	FLUX (ions·cm^2/mg)	FLUENCE (# ions)	LET_{EFF} (MeV.cm^2/mg)
22	40	125	Ag	0°	1.00E+05	1.00E+07	43

No SEL events were observed, indicating that the ISOS141-SEP is SEL-immune at LET_{EFF} = 43 MeV-cm^2/mg and T = 125°C. Using the MFTF method described in Appendix A and combining (or summing) the fluences of the two runs @ 125°C (2 × 10^7), the upper-bound cross-section (using a 95% confidence level) is calculated in Equation 1:

$$\sigma SEL \leq 1.84 \times 10^{-7}\ cm^2 \text{ for } LET_{EFF} = 43\ MeV\text{-}cm^2/mg \text{ and } T = 125°C. \tag{1}$$

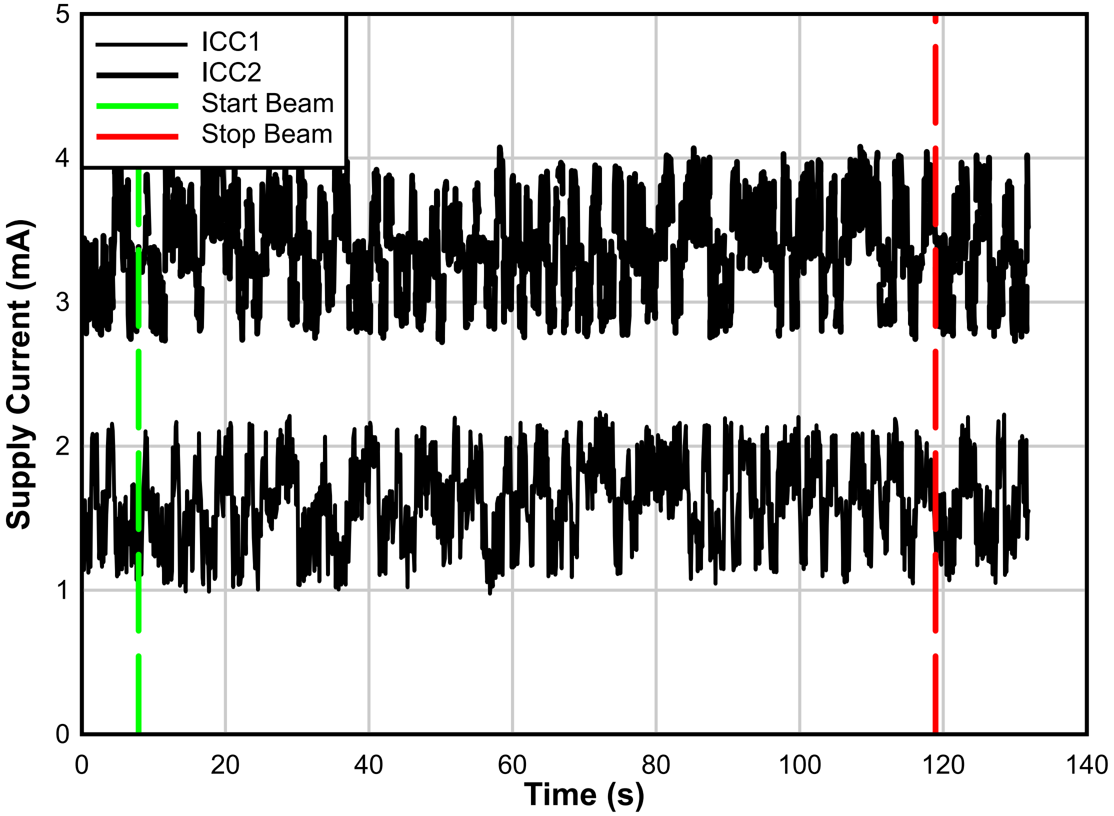

Figure 5-1. Current vs Time (I vs t) Data for Vs Current During SEL Run # 32

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5.2 Isolation Barrier SEDR Results

The ISOS141-SEP barrier isolation SEDR was tested by biasing the device at 500 V_{DC} with all pins grounded while irradiating at LET_{EFF} = 43 MeV-cm^2/mg and T = 125°C to a fluence of 3 x 10^7 ions/cm^2 and flux of 1 x 10^5 ions/s-cm^2. The resistance across the barrier was measured before and after irradiation. The resistance measured 3 TΩ before and after irradiation. The isolation barrier is rated to 500 V_{DC} over the entire recommended operation.

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6 Summary

Radiation effects of Radiation Tolerant High-Performance, Quad-Channel Digital Isolator, ISOS141-SEP, was studied. This device passed total dose rate of up to 30 krad(Si) and is latch-up immune up to LET_{EFF} = 43 MeV-cm^2/mg and T = 125°C. The device barrier isolation was immune to SEDR at LET_{EFF} = 43 MeV-cm^2/mg and T = 125°C to a fluence of 3 x 10^7 ions/cm^2 and flux of 1 x 10^5 ions/s-cm^2 at an isolation voltage of 500 V_{DC}.

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A Confidence Interval Calculations

For conventional products where hundreds of failures are seen during a single exposure, one can determine the average failure rate of parts being tested in a heavy-ion beam as a function of fluence with high degree of certainty and reasonably tight standard deviation, and thus have a good deal of confidence that the calculated cross-section is accurate.

With radiation-hardened parts however, it is difficult to determine the cross-section because often few or no failures are observed during an entire exposure. Determining the cross-section using an average failure rate with standard deviation is no longer a viable option, and the common practice of assuming a single error occurred at the conclusion of a null-result can end up in a greatly underestimated cross-section.

In cases where observed failures are rare or non-existent, the use of confidence intervals and the chi-squared distribution is indicated. The chi-squared distribution is particularly well-suited for the determination of a reliability level when the failures occur at a constant rate. In the case of SEE testing where the ion events are random in time and position within the irradiation area, one expects a failure rate that is independent of time (presuming that parametric shifts induced by the total ionizing dose do not affect the failure rate), and thus the use of chi-squared statistical techniques is valid (because events are rare, an exponential or Poisson distribution is usually used).

In a typical SEE experiment, the device-under-test (DUT) is exposed to a known, fixed fluence (ions/cm^2) while the DUT is monitored for failures. This is analogous to fixed-time reliability testing and, more specifically, time-terminated testing where the reliability test is terminated after a fixed amount of time whether or not a failure has occurred (in the case of SEE tests fluence is substituted for time and hence it is a fixed fluence test [5]). Calculating a confidence interval specifically provides a range of values which is likely to contain the parameter of interest (the actual number of failures/fluence). Confidence intervals are constructed at a specific confidence level. For example, a 95% confidence level implies that if a given number of units were sampled numerous times and a confidence interval estimated for each test, the resulting set of confidence intervals would bracket the true population parameter in about 95% of the cases.

To estimate the cross-section from a null-result (no fails observed for a given fluence) with a confidence interval, we start with the standard reliability determination of lower-bound (minimum) mean-time-to-failure for fixed-time testing (an exponential distribution is assumed) in Equation 2:

$$MTTF = \frac{2nT}{\chi^{2}_{2(d+1);\,100\left(1-\frac{\alpha}{2}\right)}} \tag{2}$$

Where:

- *MTTF* is the minimum (lower-bound) mean-time-to-failure,
- *n* is the number of units tested (presuming each unit is tested under identical conditions),
- *T* is the test time,
- and χ^2 is the chi-square distribution evaluated at 100(1 – α / 2) confidence level
- *d* is the degrees-of-freedom (the number of failures observed).

With slight modification for our purposes we invert the inequality and substitute *F* (fluence) in the place of *T* as shown in Equation 3:

$$MFTF = \frac{2nF}{\chi^{2}_{2(d+1);\,100\left(1-\frac{\alpha}{2}\right)}} \tag{3}$$

Where:

- *MFTF* is mean-fluence-to-failure
- *F* is the test fluence
- X^2 is the chi-square distribution evaluated at 100(1 – α / 2) confidence
- *d* is the degrees-of-freedom (the number of failures observed).

The inverse relation between *MTTF* and failure rate is mirrored with the *MFTF*. Thus the upper-bound cross-section is obtained by inverting the *MFTF* as shown in Equation 4:

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$$\sigma = \frac{\chi^2_{2(d+1);\,100\left(1-\frac{\alpha}{2}\right)}}{2nF} \tag{4}$$

Assume that all tests are terminated at a total fluence of 10^6 ions/cm^2. Also assume there are a number of devices with very different performances that are tested under identical conditions. Assume a 95% confidence level (σ = 0.05). Note that as *d* increases from 0 events to 100 events, the actual confidence interval becomes smaller, indicating that the range of values of the true value of the population parameter (in this case the cross-section) is approaching the mean value + 1 standard deviation. This makes sense when one considers that as more events are observed the statistics are improved such that uncertainty in the actual device performance is reduced.

Table A-1. Experimental Example Calculation of MFTF and σ Using a 95% Confidence Interval(1)

Degrees-of-Freedom (d)	2(d + 1)	χ^2 @ 95%	Calculated Cross-Section (cm^2)		
			Upper-Bound @ 95% Confidence	Mean	Average + Standard Deviation
0	2	7.38	3.69E–06	0.00E+00	0.00E+00
1	4	11.14	5.57E–06	1.00E–06	2.00E–06
2	6	14.45	7.22E–06	2.00E–06	3.41E–06
3	8	17.53	8.77E–06	3.00E–06	4.73E–06
4	10	20.48	1.02E–05	4.00E–06	6.00E–06
5	12	23.34	1.17E–05	5.00E–06	7.24E–06
10	22	36.78	1.84E–05	1.00E–05	1.32E–05
50	102	131.84	6.59E–05	5.00E–05	5.71E–05
100	202	243.25	1.22E–04	1.00E–04	1.10E–04

(1) Using a 95% confidence interval for several different observed results (d = 0, 1, 2,…100 observed events during fixed-fluence tests) assuming 10^6 ions/cm^2 for each test. Note that as the number of observed events increases the confidence interval approaches the mean.

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B References

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